547.

标题: Diameter Dependence of Sub-Terahertz AC Response of Metallic Carbon Nanotubes with a Single Atomic Vacancy

作者: Hirai, D (Hirai, Daisuke); Yamamoto, T (Yamamoto, Takahiro); Watanabe, S (Watanabe, Satoshi)

来源出版物: JAPANESE JOURNAL OF APPLIED PHYSICS 卷: 51 期: 4 特刊: SI 文献 号: 04DN01 DOI: 10.1143/JJAP.51.04DN01 子辑: Part 2 出版年: APR 2012

在 Web of Science 中的被引频次:0

被引频次合计:0

引用的参考文献数:17

摘要: The sub-THz AC response of metallic single-walled carbon nanotubes (M-SWNTs) with a single atomic vacancy is investigated theoretically focusing on its diameter dependence. We find that the AC response behaves more capacitively in large-diameter M-SWNTs with a vacancy at the center of the SWNT in contrast to the diameter-independent AC response of a pristine M-SWNT showing the inductive response. This can be understood from the fact that the large-diameter M-SWNTs with a vacancy have more scattering states for electrons around the vacancy than the small-diameter ones. In addition, the threshold of vacancy position from the center of the SWNT, beyond which the inductive response appears regardless of the Fermi level position, is higher for large-diameter M-SWNTs than for small-diameter ones. Moreover, we find that the AC response depends strongly on tube diameter, but not on the type of tube, i.e., armchair or zigzag. (C) 2012 The Japan Society of Applied Physics

入藏号: WOS:000303928600095

语种: English

文献类型: Article

KeyWords Plus: QUANTUM CONDUCTANCE; ADMITTANCE; DEFECTS; STATES

地址: [Hirai, Daisuke; Watanabe, Satoshi] Univ Tokyo, Dept Mat Engn, Bunkyo Ku, Tokyo 1138656, Japan

[Yamamoto, Takahiro] Tokyo Univ Sci, Fac Engn, Dept Liberal Arts Phys, Tokyo, Tokyo 1020073, Japan

通讯作者地址: Hirai, D (通讯作者), Univ Tokyo, Dept Mat Engn, Bunkyo Ku, Tokyo 1138656, Japan

电子邮件地址: daisuke.hirai@cello.t.u-tokyo.ac.jp

出版商: JAPAN SOC APPLIED PHYSICS

出版商地址: KUDAN-KITA BUILDING 5TH FLOOR, 1-12-3 KUDAN-KITA, CHIYODA-KU,

TOKYO, 102-0073, JAPAN

Web of Science 分类: Physics, Applied

学科类别: Physics

IDS 号: 940YI

ISSN: 0021-4922

29 字符的来源出版物名称缩写: JPN J APPL PHYS

ISO 来源出版物缩写: Jpn. J. Appl. Phys.

来源出版物页码计数:5